

Supplementary Materials: High Performance Complementary Circuits Based on p-SnO and n-IGZO Thin-Film Transistors

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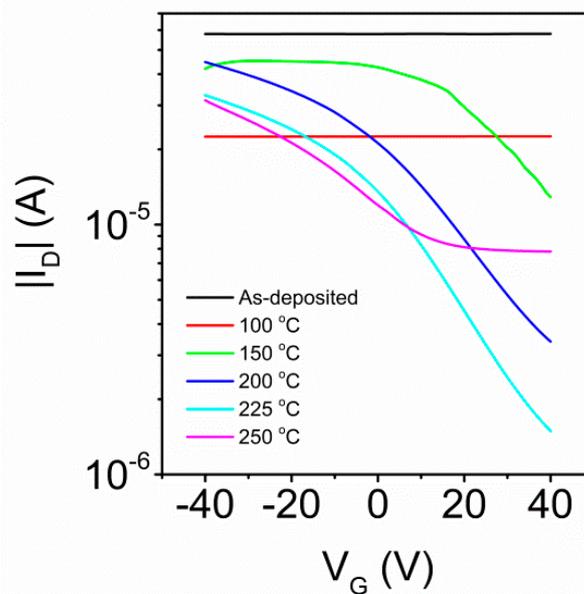


Figure S1. Transfer characteristics of the SnO TFTs annealed at different temperatures at $V_D = -1$ V.

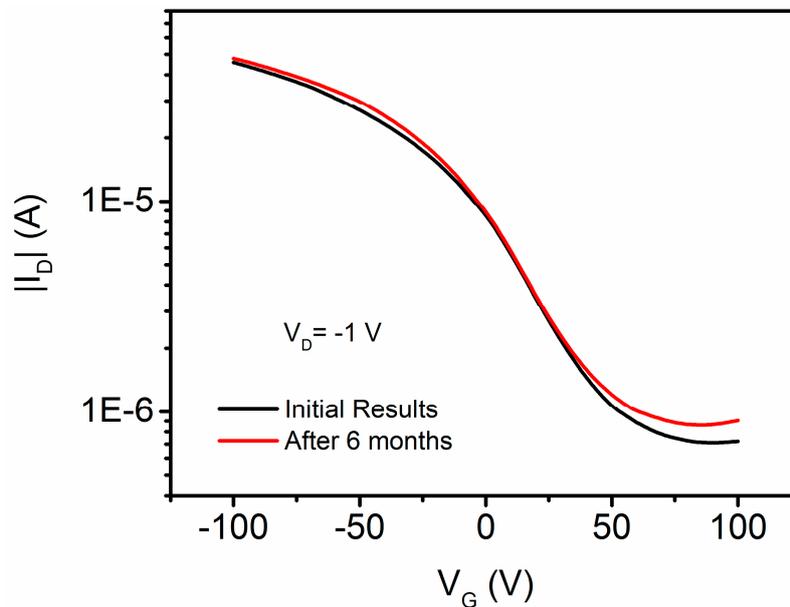


Figure S2. Transfer characteristics of the SnO TFT annealed at 225 °C measured immediately after the fabrication and after 6 months in air, respectively.

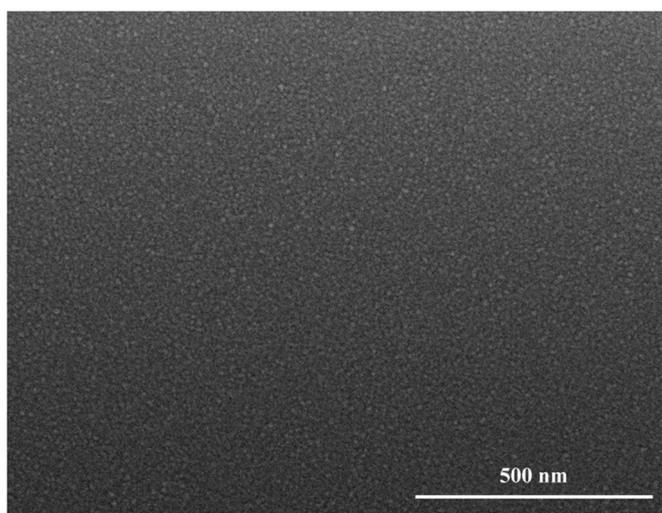


Figure S3. SEM image of the as-deposited SnO film.

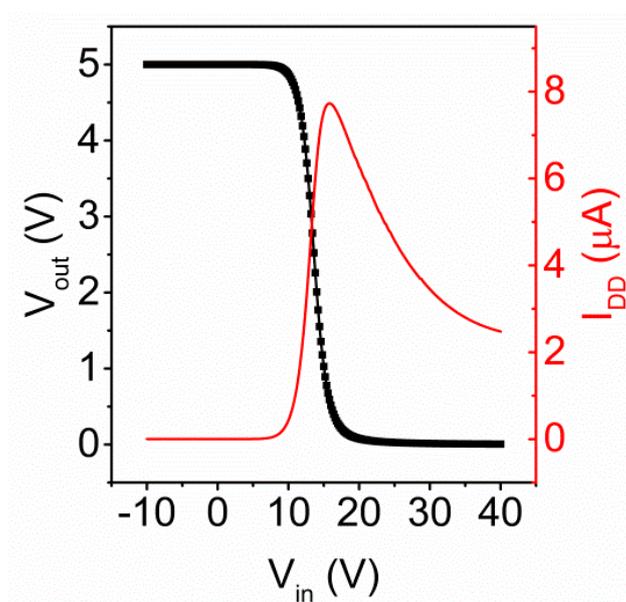


Figure S4. Output voltage and the leakage current of the inverter with $V_{DD} = 5$ V.